## IGBT-Wechselrichter / IGBT-inverter

**Vorläufige Daten / preliminary data**

### Höchstzulässige Werte / maximum rated values

| | | | | |
|---|---|---|---|---|
| Kollektor-Emitter-Sperrspannung<br>collector-emitter voltage | $T_{vj}$ = 25°C | $V_{CES}$ | 1200 | V |
| Kollektor-Dauergleichstrom<br>DC-collector current | $T_C$ = 80°C, $T_{vj}$ = 150°C<br>$T_C$ = 25°C, $T_{vj}$ = 150°C | $I_{C\ nom}$<br>$I_C$ | 10<br>16 | A<br>A |
| Periodischer Kollektor Spitzenstrom<br>repetitive peak collector current | $t_P$ = 1 ms | $I_{CRM}$ | 20 | A |
| Gesamt-Verlustleistung<br>total power dissipation | $T_C$ = 25°C, $T_{vj}$ = 150°C | $P_{tot}$ | 69,5 | W |
| Gate-Emitter-Spitzenspannung<br>gate-emitter peak voltage | | $V_{GES}$ | +/-20 | V |

### Charakteristische Werte / characteristic values

| | | | min. | typ. | max. | |
|---|---|---|---|---|---|---|
| Kollektor-Emitter Sättigungsspannung<br>collector-emitter saturation voltage | $I_C$ = 10 A, $V_{GE}$ = 15 V<br>$I_C$ = 10 A, $V_{GE}$ = 15 V | $T_{vj}$ = 25°C<br>$T_{vj}$ = 125°C | $V_{CE\ sat}$ | | 1,90<br>2,15 | 2,45 | V<br>V |
| Gate-Schwellenspannung<br>gate threshold voltage | $I_C$ = 0,30 mA, $V_{CE}$ = $V_{GE}$, $T_{vj}$ = 25°C | | $V_{GEth}$ | 5,0 | 5,8 | 6,5 | V |
| Gateladung<br>gate charge | $V_{GE}$ = -15 V ... +15 V | | $Q_G$ | | 0,10 | | µC |
| Interner Gatewiderstand<br>internal gate resistor | $T_{vj}$ = 25°C | | $R_{Gint}$ | | 0,0 | | Ω |
| Eingangskapazität<br>input capacitance | f = 1 MHz, $T_{vj}$ = 25°C, $V_{CE}$ = 25 V, $V_{GE}$ = 0 V | | $C_{ies}$ | | 0,70 | | nF |
| Rückwirkungskapazität<br>reverse transfer capacitance | f = 1 MHz, $T_{vj}$ = 25°C, $V_{CE}$ = 25 V, $V_{GE}$ = 0 V | | $C_{res}$ | | 0,026 | | nF |
| Kollektor-Emitter Reststrom<br>collector-emitter cut-off current | $V_{CE}$ = 1200 V, $V_{GE}$ = 0 V, $T_{vj}$ = 25°C | | $I_{CES}$ | | | 1,0 | mA |
| Gate-Emitter Reststrom<br>gate-emitter leakage current | $V_{CE}$ = 0 V, $V_{GE}$ = 20 V, $T_{vj}$ = 25°C | | $I_{GES}$ | | | 400 | nA |
| Einschaltverzögerungszeit (ind. Last)<br>turn-on delay time (inductive load) | $I_C$ = 10 A, $V_{CE}$ = 600 V<br>$V_{GE}$ = ±15 V<br>$R_{Gon}$ = 82 Ω | $T_{vj}$ = 25°C<br>$T_{vj}$ = 125°C | $t_{d\ on}$ | | 0,045<br>0,045 | | µs<br>µs |
| Anstiegszeit (induktive Last)<br>rise time (inductive load) | $I_C$ = 10 A, $V_{CE}$ = 600 V<br>$V_{GE}$ = ±15 V<br>$R_{Gon}$ = 82 Ω | $T_{vj}$ = 25°C<br>$T_{vj}$ = 125°C | $t_r$ | | 0,02<br>0,025 | | µs<br>µs |
| Abschaltverzögerungszeit (ind. Last)<br>turn-off delay time (inductive load) | $I_C$ = 10 A, $V_{CE}$ = 600 V<br>$V_{GE}$ = ±15 V<br>$R_{Goff}$ = 82 Ω | $T_{vj}$ = 25°C<br>$T_{vj}$ = 125°C | $t_{d\ off}$ | | 0,29<br>0,39 | | µs<br>µs |
| Fallzeit (induktive Last)<br>fall time (inductive load) | $I_C$ = 10 A, $V_{CE}$ = 600 V<br>$V_{GE}$ = ±15 V<br>$R_{Goff}$ = 82 Ω | $T_{vj}$ = 25°C<br>$T_{vj}$ = 125°C | $t_f$ | | 0,09<br>0,15 | | µs<br>µs |
| Einschaltverlustenergie pro Puls<br>turn-on energy loss per pulse | $I_C$ = 10 A, $V_{CE}$ = 600 V<br>$V_{GE}$ = ±15 V, $L_S$ = 50 nH<br>$R_{Gon}$ = 82 Ω | $T_{vj}$ = 25°C<br>$T_{vj}$ = 125°C | $E_{on}$ | | 0,95<br>1,35 | | mJ<br>mJ |
| Abschaltverlustenergie pro Puls<br>turn-off energy loss per pulse | $I_C$ = 10 A, $V_{CE}$ = 600 V<br>$V_{GE}$ = ±15 V, $L_S$ = 50 nH<br>$R_{Goff}$ = 82 Ω | $T_{vj}$ = 25°C<br>$T_{vj}$ = 125°C | $E_{off}$ | | 0,67<br>1,05 | | mJ<br>mJ |
| Kurzschlussverhalten<br>SC data | $V_{GE}$ ≤ 15 V, $V_{CC}$ = 900 V<br>$V_{CEmax}$ = $V_{CES}$ -$L_{sCE}$ ·di/dt | $t_P$ ≤ 10 µs, $T_{vj}$ = 125°C | $I_{SC}$ | | 35 | | A |
| Innerer Wärmewiderstand<br>thermal resistance, junction to case | pro IGBT<br>per IGBT | | $R_{thJC}$ | | 1,60 | 1,80 | K/W |
| Übergangs-Wärmewiderstand<br>thermal resistance, case to heatsink | pro IGBT / per IGBT<br>$\lambda_{Paste}$ = 1 W/(m·K) / $\lambda_{grease}$ = 1 W/(m·K) | | $R_{thCH}$ | | 0,55 | | K/W |

| | |
|---|---|
| prepared by: Peter Kanschat | date of publication: 2005-6-15 |
| approved by: Ralf Keggenhoff | revision: 2.0 |

**Vorläufige Daten**
**preliminary data**

## Diode-Wechselrichter / diode-inverter

### Höchstzulässige Werte / maximum rated values

| | | | | | |
|---|---|---|---|---|---|
| Periodische Spitzensperrspannung<br>repetitive peak reverse voltage | $T_{vj}$ = 25°C | $V_{RRM}$ | 1200 | | V |
| Dauergleichstrom<br>DC forward current | | $I_F$ | 10 | | A |
| Periodischer Spitzenstrom<br>repetitive peak forward current | $t_P$ = 1 ms | $I_{FRM}$ | 20 | | A |
| Grenzlastintegral<br>I²t - value | $V_R$ = 0 V, $t_P$ = 10 ms, $T_{vj}$ = 125°C | I²t | 20,0 | | A²s |

### Charakteristische Werte / characteristic values

| | | | min. | typ. | max. | |
|---|---|---|---|---|---|---|
| Durchlassspannung<br>forward voltage | $I_F$ = 10 A, $V_{GE}$ = 0 V, $T_{vj}$ = 25°C<br>$I_F$ = 10 A, $V_{GE}$ = 0 V, $T_{vj}$ = 125°C | $V_F$ | | 1,65<br>1,65 | 2,10 | V<br>V |
| Rückstromspitze<br>peak reverse recovery current | $I_F$ = 10 A, - $di_F/dt$ = 650 A/µs, $T_{vj}$ = 25°C<br>$V_R$ = 600 V, $T_{vj}$ = 125°C<br>$V_{GE}$ = -15 V | $I_{RM}$ | | 16,0<br>16,0 | | A<br>A |
| Sperrverzögerungsladung<br>recovered charge | $I_F$ = 10 A, - $di_F/dt$ = 650 A/µs, $T_{vj}$ = 25°C<br>$V_R$ = 600 V, $T_{vj}$ = 125°C<br>$V_{GE}$ = -15 V | $Q_r$ | | 1,00<br>1,80 | | µC<br>µC |
| Abschaltenergie pro Puls<br>reverse recovery energy | $I_F$ = 10 A, - $di_F/dt$ = 650 A/µs, $T_{vj}$ = 25°C<br>$V_R$ = 600 V, $T_{vj}$ = 125°C<br>$V_{GE}$ = -15 V | $E_{rec}$ | | 0,33<br>0,63 | | mJ<br>mJ |
| Innerer Wärmewiderstand<br>thermal resistance, junction to case | pro Diode<br>per diode | $R_{thJC}$ | | 1,95 | 2,20 | K/W |
| Übergangs-Wärmewiderstand<br>thermal resistance, case to heatsink | pro Diode / per diode<br>$\lambda_{Paste}$ = 1 W/(m·K) / $\lambda_{grease}$ = 1 W/(m·K) | $R_{thCH}$ | | 0,65 | | K/W |

## Diode-Gleichrichter / diode-rectifier

### Höchstzulässige Werte / maximum rated values

| | | | | | |
|---|---|---|---|---|---|
| Periodische Rückw. Spitzensperrspannung<br>repetitive peak reverse voltage | $T_{vj}$ = 25°C | $V_{RRM}$ | 1600 | | V |
| Durchlassstrom Grenzeffektivwert pro Dio.<br>forward current RMS maximum per diode | $T_C$ = 80°C | $I_{FRMSM}$ | 25 | | A |
| Gleichrichter Ausgang Grenzeffektivstrom<br>maximum RMS current at Rectifier output | $T_C$ = 80°C | $I_{RMSM}$ | 25 | | A |
| Stoßstrom Grenzwert<br>surge forward current | $t_p$ = 10 ms, $T_{vj}$ = 25°C<br>$t_p$ = 10 ms, $T_{vj}$ = 150°C | $I_{FSM}$ | 300<br>230 | | A<br>A |
| Grenzlastintegral<br>I²t - value | $t_p$ = 10 ms, $T_{vj}$ = 25°C<br>$t_p$ = 10 ms, $T_{vj}$ = 150°C | I²t | 450<br>265 | | A²s<br>A²s |

### Charakteristische Werte / characteristic values

| | | | min. | typ. | max. | |
|---|---|---|---|---|---|---|
| Durchlassspannung<br>forward voltage | $T_{vj}$ = 150°C, $I_F$ = 10 A | $V_F$ | | 0,85 | | V |
| Schleusenspannung<br>threshold voltage | $T_{vj}$ = 150°C | $V_{TO}$ | | 0,71 | | V |
| Ersatzwiderstand<br>slope resistance | $T_{vj}$ = 150°C | $r_T$ | | 15,0 | | mΩ |
| Sperrstrom<br>reverse current | $T_{vj}$ = 150°C, $V_R$ = 1600 V | $I_R$ | | 2,00 | | mA |
| Innerer Wärmewiderstand<br>thermal resistance, junction to case | pro Diode<br>per diode | $R_{thJC}$ | | 1,25 | 1,40 | K/W |
| Übergangs-Wärmewiderstand<br>thermal resistance, case to heatsink | pro Diode / per diode<br>$\lambda_{Paste}$ = 1 W/(m·K) / $\lambda_{grease}$ = 1 W/(m·K) | $R_{thCH}$ | | 0,55 | | K/W |



| | |
|---|---|
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**Vorläufige Daten**
**preliminary data**

## IGBT-Brems-Chopper / IGBT-brake-chopper

### Höchstzulässige Werte / maximum rated values

| | | | | |
|---|---|---|---|---|
| Kollektor-Emitter-Sperrspannung<br>collector-emitter voltage | $T_{vj}$ = 25°C | $V_{CES}$ | 1200 | V |
| Kollektor-Dauergleichstrom<br>DC-collector current | $T_C$ = 80°C, $T_{vj}$ = 150°C<br>$T_C$ = 25°C, $T_{vj}$ = 150°C | $I_{Cnom}$<br>$I_C$ | 10<br>16 | A<br>A |
| Periodischer Kollektor Spitzenstrom<br>repetitive peak collector current | $t_P$ = 1 ms | $I_{CRM}$ | 20 | A |
| Gesamt-Verlustleistung<br>total power dissipation | $T_C$ = 25°C, $T_{vj}$ = 150°C | $P_{tot}$ | 69,5 | W |
| Gate-Emitter-Spitzenspannung<br>gate-emitter peak voltage | | $V_{GES}$ | +/-20 | V |

### Charakteristische Werte / characteristic values

| | | | min. | typ. | max. | |
|---|---|---|---|---|---|---|
| Kollektor-Emitter Sättigungsspannung<br>collector-emitter saturation voltage | $I_C$ = 10 A, $V_{GE}$ = 15 V<br>$I_C$ = 10 A, $V_{GE}$ = 15 V | $T_{vj}$ = 25°C<br>$T_{vj}$ = 125°C | $V_{CE\ sat}$ | | 1,90<br>2,15 | 2,45 | V<br>V |
| Gate-Schwellenspannung<br>gate threshold voltage | $I_C$ = 0,30 mA, $V_{CE}$ = $V_{GE}$, $T_{vj}$ = 25°C | | $V_{GEth}$ | 5,0 | 5,8 | 6,5 | V |
| Gateladung<br>gate charge | $V_{GE}$ = -15 V ... +15 V | | $Q_G$ | | 0,10 | | µC |
| Interner Gatewiderstand<br>internal gate resistor | $T_{vj}$ = 25°C | | $R_{Gint}$ | | 0,00 | | Ω |
| Eingangskapazität<br>input capacitance | f = 1 MHz, $T_{vj}$ = 25°C, $V_{CE}$ = 25 V, $V_{GE}$ = 0 V | | $C_{ies}$ | | 0,70 | | nF |
| Rückwirkungskapazität<br>reverse transfer capacitance | f = 1 MHz, $T_{vj}$ = 25°C, $V_{CE}$ = 25 V, $V_{GE}$ = 0 V | | $C_{res}$ | | 0,026 | | nF |
| Kollektor-Emitter Reststrom<br>collector-emitter cut-off current | $V_{CE}$ = 1200 V, $V_{GE}$ = 0 V, $T_{vj}$ = 25°C | | $I_{CES}$ | | | 1,0 | mA |
| Gate-Emitter Reststrom<br>gate-emitter leakage current | $V_{CE}$ = 0 V, $V_{GE}$ = 20 V, $T_{vj}$ = 25°C | | $I_{GES}$ | | | 400 | nA |
| Einschaltverzögerungszeit (ind. Last)<br>turn-on delay time (inductive load) | $I_C$ = 10 A, $V_{CE}$ = 600 V<br>$V_{GE}$ = ±15 V<br>$R_{Gon}$ = 82 Ω | $T_{vj}$ = 25°C<br>$T_{vj}$ = 125°C | $t_{d\ on}$ | | 0,045<br>0,045 | | µs<br>µs |
| Anstiegszeit (induktive Last)<br>rise time (inductive load) | $I_C$ = 10 A, $V_{CE}$ = 600 V<br>$V_{GE}$ = ±15 V<br>$R_{Gon}$ = 82 Ω | $T_{vj}$ = 25°C<br>$T_{vj}$ = 125°C | $t_r$ | | 0,02<br>0,025 | | µs<br>µs |
| Abschaltverzögerungszeit (ind. Last)<br>turn-off delay time (inductive load) | $I_C$ = 10 A, $V_{CE}$ = 600 V<br>$V_{GE}$ = ±15 V<br>$R_{Goff}$ = 82 Ω | $T_{vj}$ = 25°C<br>$T_{vj}$ = 125°C | $t_{d\ off}$ | | 0,28<br>0,39 | | µs<br>µs |
| Fallzeit (induktive Last)<br>fall time (inductive load) | $I_C$ = 10 A, $V_{CE}$ = 600 V<br>$V_{GE}$ = ±15 V<br>$R_{Goff}$ = 82 Ω | $T_{vj}$ = 25°C<br>$T_{vj}$ = 125°C | $t_f$ | | 0,09<br>0,15 | | µs<br>µs |
| Einschaltverlustenergie pro Puls<br>turn-on energy loss per pulse | $I_C$ = 10 A, $V_{CE}$ = 600 V<br>$V_{GE}$ = ±15 V<br>$R_{Gon}$ = 82 Ω | $T_{vj}$ = 25°C<br>$T_{vj}$ = 125°C | $E_{on}$ | | 0,85<br>1,15 | | mJ<br>mJ |
| Abschaltverlustenergie pro Puls<br>turn-off energy loss per pulse | $I_C$ = 10 A, $V_{CE}$ = 600 V<br>$V_{GE}$ = ±15 V<br>$R_{Goff}$ = 82 Ω | $T_{vj}$ = 25°C<br>$T_{vj}$ = 125°C | $E_{off}$ | | 0,67<br>1,05 | | mJ<br>mJ |
| Kurzschlussverhalten<br>SC data | $V_{GE}$ ≤ 15 V, $V_{CC}$ = 900 V<br>$V_{CEmax}$ = $V_{CES}$ -$L_{sCE}$ · di/dt | $t_P$ ≤ 10 µs, $T_{vj}$ = 125°C | $I_{SC}$ | | 35 | | A |
| Innerer Wärmewiderstand<br>thermal resistance, junction to case | pro IGBT<br>per IGBT | | $R_{thJC}$ | | 1,60 | 1,80 | K/W |
| Übergangs-Wärmewiderstand<br>thermal resistance, case to heatsink | pro IGBT / per IGBT<br>$\lambda_{Paste}$ = 1 W/(m·K) / $\lambda_{grease}$ = 1 W/(m·K) | | $R_{thCH}$ | | 0,55 | | K/W |

**Vorläufige Daten**
**preliminary data**

## Diode-Brems-Chopper / Diode-brake-chopper

### Höchstzulässige Werte / maximum rated values

| | | | | |
|---|---|---|---|---|
| Periodische Spitzensperrspannung<br>repetitive peak reverse voltage | $T_{vj}$ = 25°C | $V_{RRM}$ | 1200 | V |
| Dauergleichstrom<br>DC forward current | | $I_F$ | 10 | A |
| Periodischer Spitzenstrom<br>repetitive peak forw. current | $t_p$ = 1 ms | $I_{FRM}$ | 20 | A |
| Grenzlastintegral<br>I²t - value | $V_R$ = 0 V, $t_P$ = 10 ms, $T_{vj}$ = 125°C | I²t | 11,0 | A²s |

### Charakteristische Werte / characteristic values

| | | | min. | typ. | max. | |
|---|---|---|---|---|---|---|
| Durchlassspannung<br>forward voltage | $I_F$ = 10 A, $V_{GE}$ = 0 V<br>$I_F$ = 10 A, $V_{GE}$ = 0 V | $T_{vj}$ = 25°C<br>$T_{vj}$ = 125°C | $V_F$ | | 1,85<br>1,90 | 2,30 | V<br>V |
| Rückstromspitze<br>peak reverse recovery current | $I_F$ = 10 A, - $di_F/dt$ = 650 A/µs<br>$V_R$ = 600 V<br>$V_{GE}$ = -15 V | $T_{vj}$ = 25°C<br>$T_{vj}$ = 125°C | $I_{RM}$ | | 12,0<br>12,0 | | A<br>A |
| Sperrverzögerungsladung<br>recovered charge | $I_F$ = 10 A, - $di_F/dt$ = 650 A/µs<br>$V_R$ = 600 V<br>$V_{GE}$ = -15 V | $T_{vj}$ = 25°C<br>$T_{vj}$ = 125°C | $Q_r$ | | 0,80<br>1,50 | | µC<br>µC |
| Abschaltenergie pro Puls<br>reverse recovery energy | $I_F$ = 10 A, - $di_F/dt$ = 650 A/µs<br>$V_R$ = 600 V<br>$V_{GE}$ = -15 V | $T_{vj}$ = 25°C<br>$T_{vj}$ = 125°C | $E_{rec}$ | | 0,30<br>0,55 | | mJ<br>mJ |
| Innerer Wärmewiderstand<br>thermal resistance, junction to case | pro Diode<br>per diode | | $R_{thJC}$ | | 2,50 | 2,80 | K/W |
| Übergangs-Wärmewiderstand<br>thermal resistance, case to heatsink | pro Diode / per diode<br>$\lambda_{Paste}$ = 1 W/(m·K) / $\lambda_{grease}$ = 1 W/(m·K) | | $R_{thCH}$ | | 0,75 | | K/W |

## NTC-Widerstand / NTC-thermistor

### Charakteristische Werte / characteristic values

| | | | min. | typ. | max. | |
|---|---|---|---|---|---|---|
| Nennwiderstand<br>rated resistance | $T_C$ = 25°C | $R_{25}$ | | 5,00 | | kΩ |
| Abweichung von $R_{100}$<br>deviation of $R_{100}$ | $T_C$ = 100°C, $R_{100}$ = 493 Ω | ΔR/R | -5 | | 5 | % |
| Verlustleistung<br>power dissipation | $T_C$ = 25°C | $P_{25}$ | | | 20,0 | mW |
| B-Wert<br>B-value | $R_2 = R_{25} \exp [B_{25/50}(1/T_2 - 1/(298{,}15\ K))]$ | $B_{25/50}$ | | 3375 | | K |

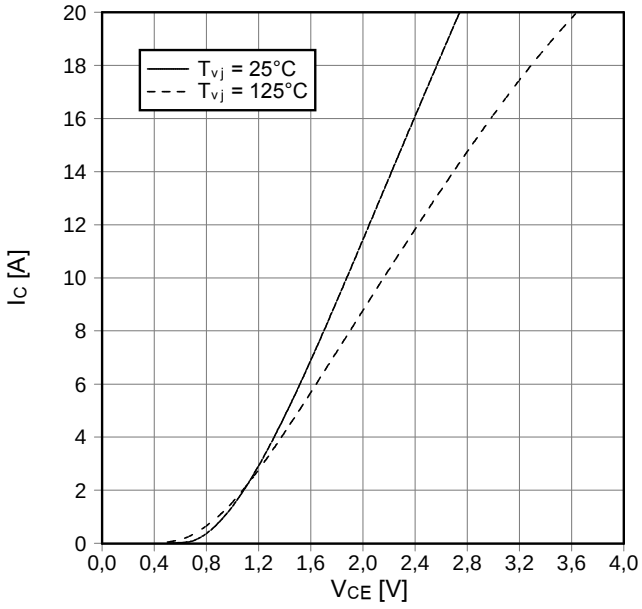
**Vorläufige Daten**
**preliminary data**

## Modul / module

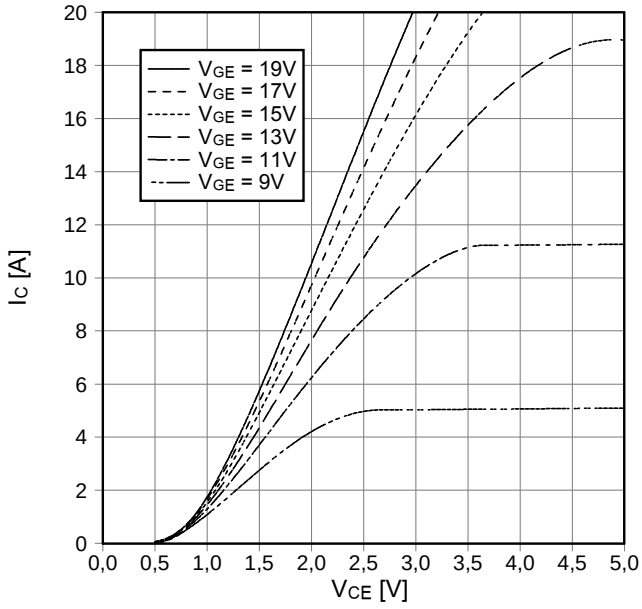
| | | | | | | |
|---|---|---|---|---|---|---|
| Isolations-Prüfspannung<br>insulation test voltage | RMS, f = 50 Hz, t = 1 min | $V_{ISOL}$ | | 2,5 | | kV |
| Material für innere Isolation<br>material for internal insulation | | | | $Al_2O_3$ | | |
| Kriechstrecke<br>creepage distance | Kontakt - Kühlkörper / terminal to heatsink<br>Kontakt - Kontakt / terminal to terminal | | | 13,5<br>7,5 | | mm |
| Luftstrecke<br>clearance distance | Kontakt - Kühlkörper / terminal to heatsink<br>Kontakt - Kontakt / terminal to terminal | | | 12,0<br>7,5 | | mm |
| Vergleichszahl der Kriechwegbildung<br>comparative tracking index | | CTI | | > 225 | | |
| | | | min. | typ. | max. | |
| Modulinduktivität<br>stray inductance module | | $L_{sCE}$ | | 40 | | nH |
| Modulleitungswiderstand, Anschlüsse - Chip<br>module lead resistance, terminals - chip | $T_C$ = 25°C, pro Schalter / per switch | $R_{CC'+EE'}$<br>$R_{AA'+CC'}$ | | 10,0<br>7,00 | | mΩ |
| Höchstzulässige Sperrschichttemperatur<br>maximum junction temperature | Wechselrichter, Brems-Chopper / Inverter, Brake-Chopper | $T_{vj\ max}$ | | | 150 | °C |
| Temperatur im Schaltbetrieb<br>temperature under switching conditions | Wechselrichter, Brems-Chopper / Inverter, Brake-Chopper | $T_{vj\ op}$ | -40 | | 125 | °C |
| Lagertemperatur<br>storage temperature | | $T_{stg}$ | -40 | | 125 | °C |
| Anpresskraft für mech. Bef. pro Feder<br>mountig force per clamp | | F | 40 | - | 80 | N |
| Gewicht<br>weight | | G | | 36 | | g |

**Vorläufige Daten**
**preliminary data**

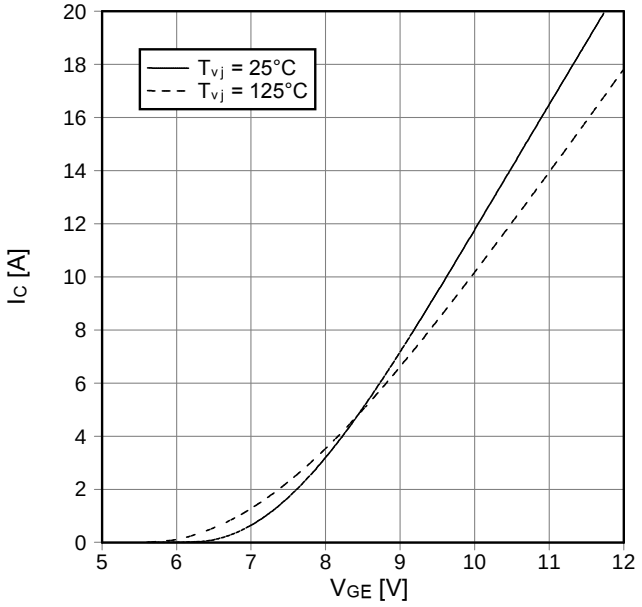
**Ausgangskennlinie IGBT-Wechselr. (typisch)**
**output characteristic IGBT-inverter (typical)**
**$I_C = f(V_{CE})$**
**$V_{GE}$ = 15 V**



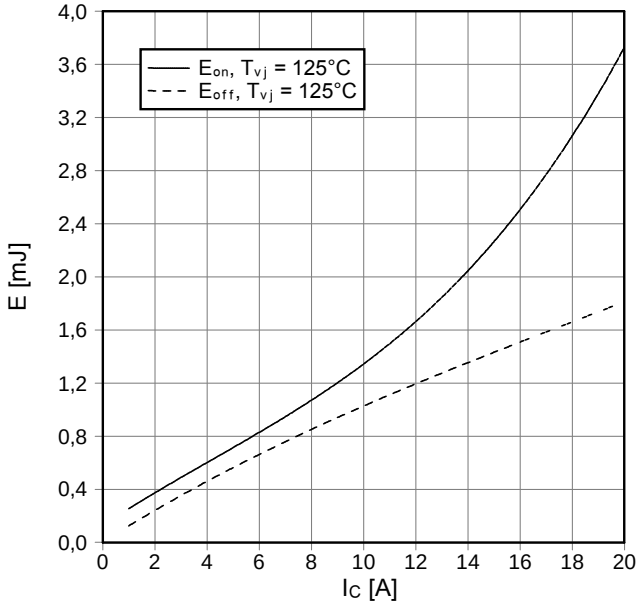

**Ausgangskennlinienfeld IGBT-Wechselr. (typisch)**
**output characteristic IGBT-inverter (typical)**
**$I_C = f(V_{CE})$**
**$T_{vj}$ = 125°C**




**Übertragungscharakteristik IGBT-Wechselr. (typisch)**
**transfer characteristic IGBT-inverter (typical)**
**$I_C = f(V_{GE})$**
**$V_{CE}$ = 20 V**




**Schaltverluste IGBT-Wechselr. (typisch)**
**switching losses IGBT-inverter (typical)**
**$E_{on} = f(I_C)$, $E_{off} = f(I_C)$**
**$V_{GE}$ = ±15 V, $R_{Gon}$ = 82 Ω, $R_{Goff}$ = 82 Ω, $V_{CE}$ = 600 V**

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|---|---|
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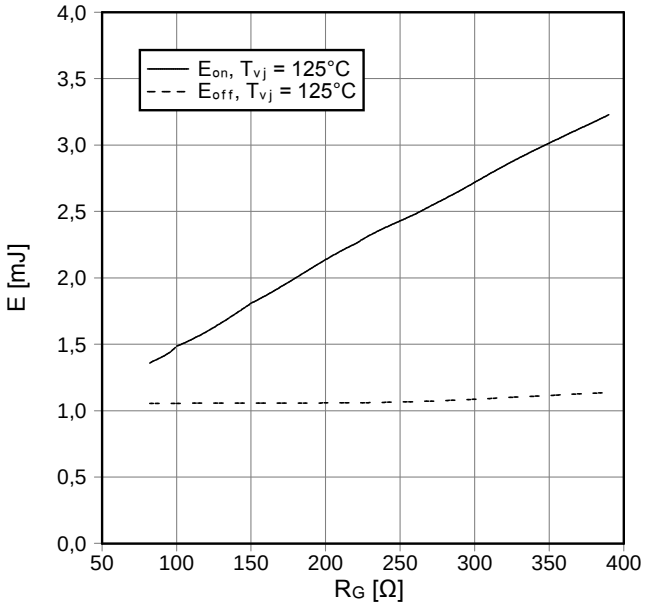
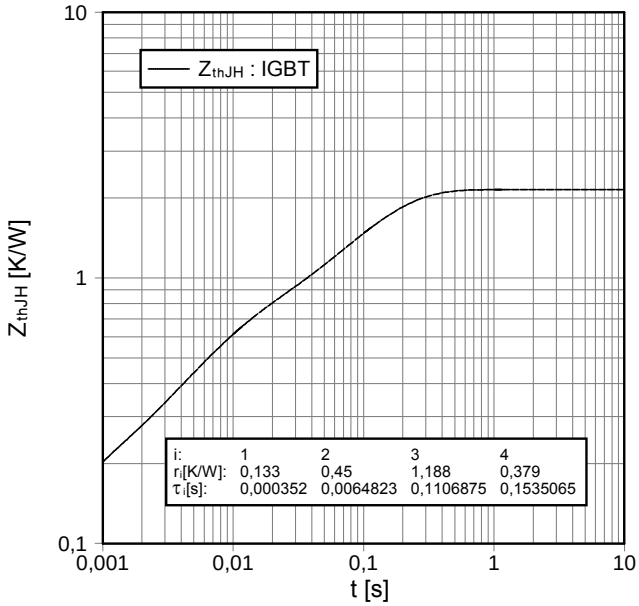
**Vorläufige Daten**
**preliminary data**

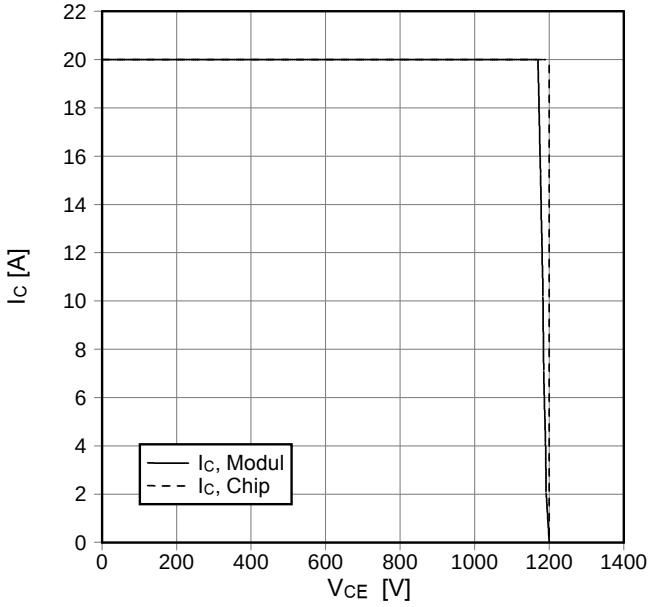
**Schaltverluste IGBT-Wechselr. (typisch)**
**switching losses IGBT-Inverter (typical)**
**$E_{on}$ = f ($R_G$), $E_{off}$ = f ($R_G$)**
**$V_{GE}$ = ±15 V, $I_C$ = 10 A, $V_{CE}$ = 600 V**



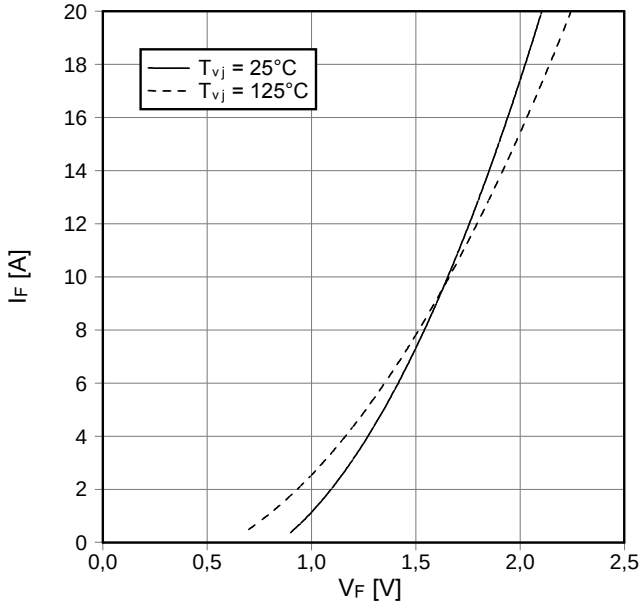

**Transienter Wärmewiderstand IGBT-Wechselr.**
**transient thermal impedance IGBT-inverter**
**$Z_{thJH}$ = f (t)**




**Sicherer Rückwärts-Arbeitsbereich IGBT-Wr. (RBSOA)**
**reverse bias safe operating area IGBT-inv. (RBSOA)**
**$I_C$ = f ($V_{CE}$)**
**$V_{GE}$ = ±15 V, $R_{Goff}$ = 82 Ω, $T_{vj}$ = 125°C**




**Durchlasskennlinie der Diode-Wechselr. (typisch)**
**forward characteristic of diode-inverter (typical)**
**$I_F$ = f ($V_F$)**

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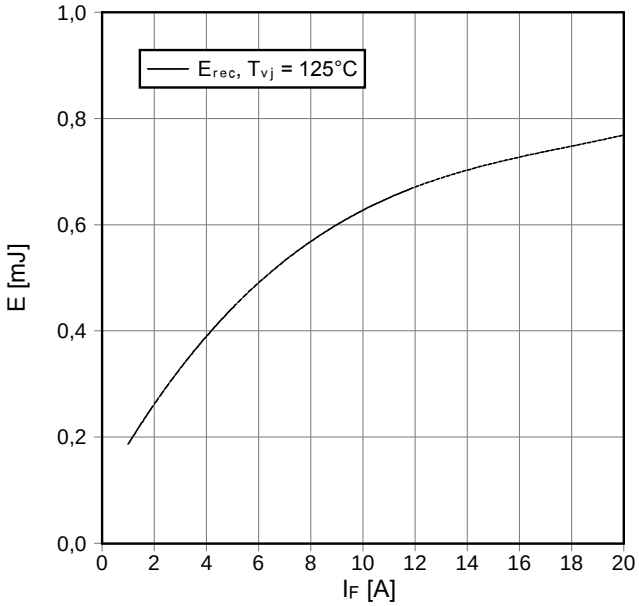
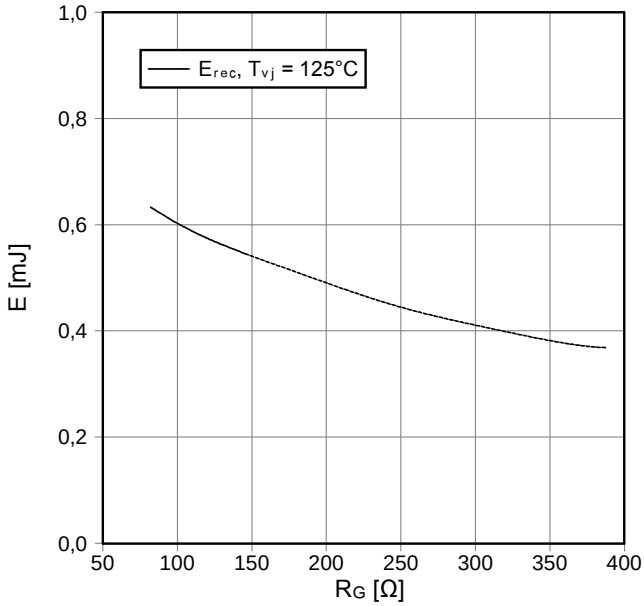
**Vorläufige Daten**
**preliminary data**

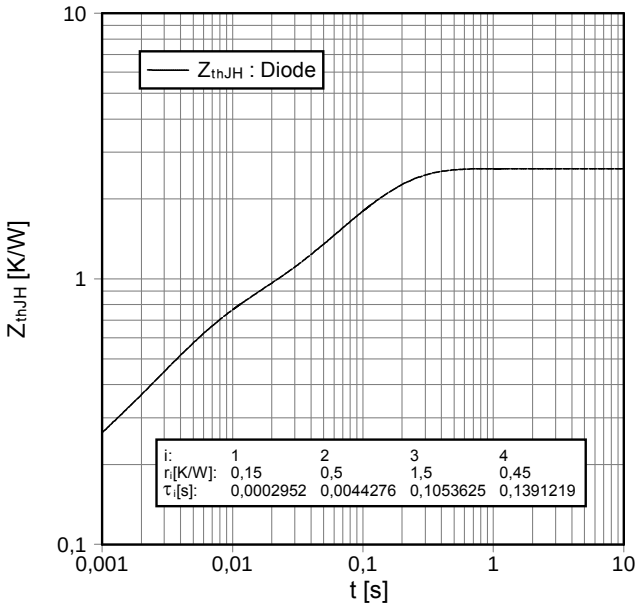
**Schaltverluste Diode-Wechselr. (typisch)**
**switching losses diode-inverter (typical)**
**$E_{rec} = f(I_F)$**
**$R_{Gon} = 82\ \Omega$, $V_{CE} = 600$ V**



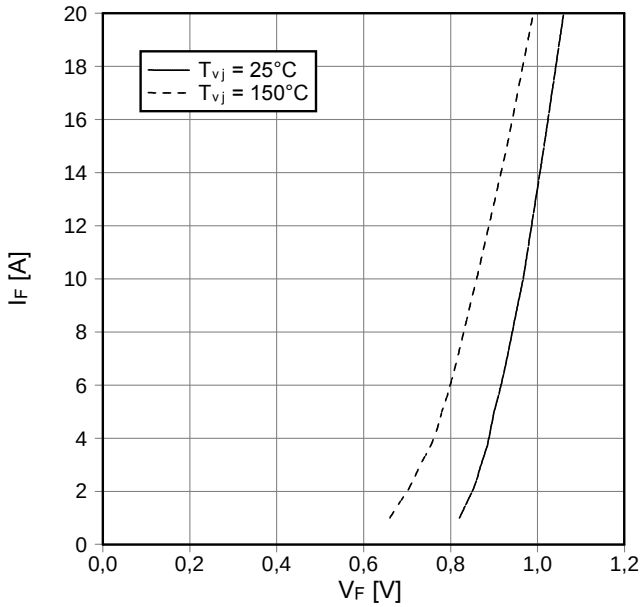

**Schaltverluste Diode-Wechselr. (typisch)**
**switching losses diode-inverter (typical)**
**$E_{rec} = f(R_G)$**
**$I_F = 10$ A, $V_{CE} = 600$ V**




**Transienter Wärmewiderstand Diode-Wechselr.**
**transient thermal impedance diode-inverter**
**$Z_{thJH} = f(t)$**




**Durchlasskennlinie der Diode-Gleichrichter (typisch)**
**forward characteristic of diode-rectifier (typical)**
**$I_F = f(V_F)$**

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**Vorläufige Daten**
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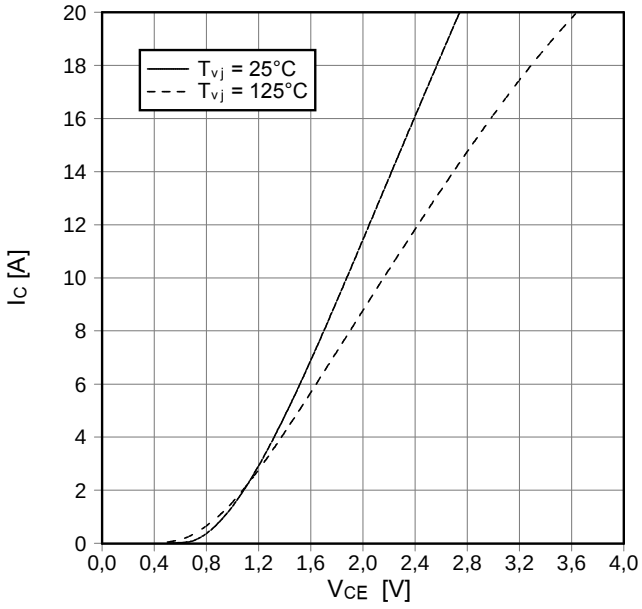
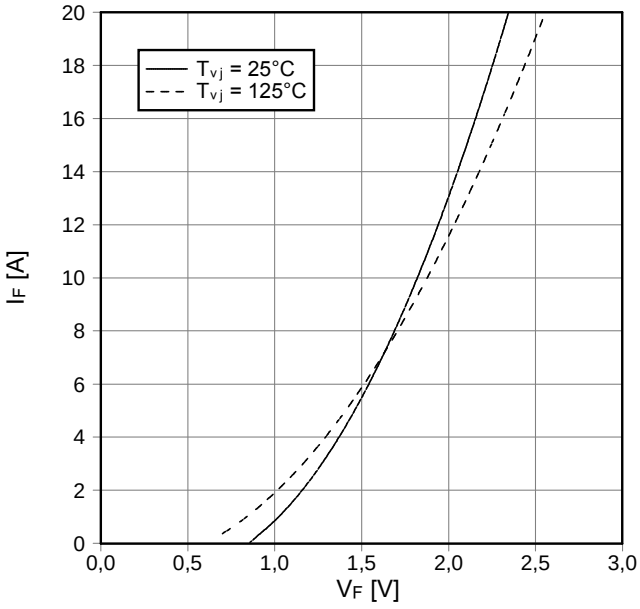
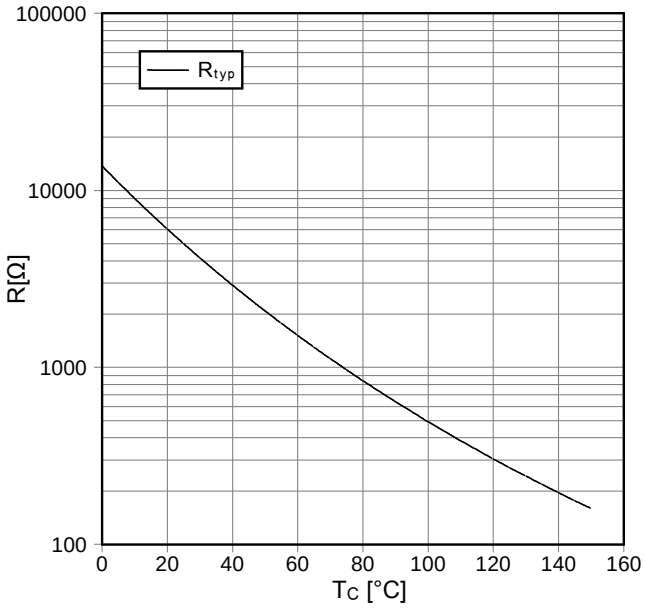
**Ausgangskennlinie IGBT-Brems-Copper (typisch)**
**output characteristic IGBT-brake-chopper (typical)**
**$I_C = f(V_{CE})$**
**$V_{GE}$ = 15 V**




**Durchlasskennlinie der Diode-Brems-Chopper (typisch)**
**forward characteristic of diode-brake-chopper (typical)**
**$I_F = f(V_F)$**




**NTC-Temperaturkennlinie (typisch)**
**NTC-temperature characteristic (typical)**
**R = f (T)**

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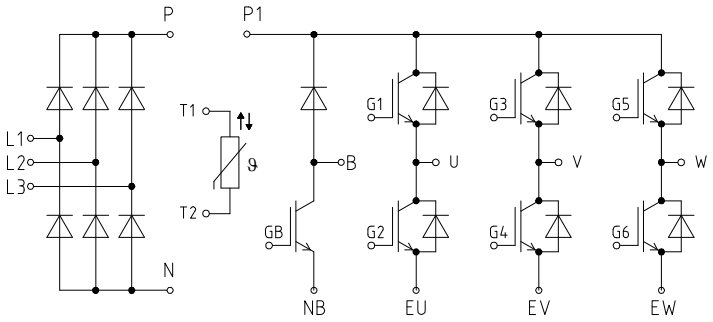
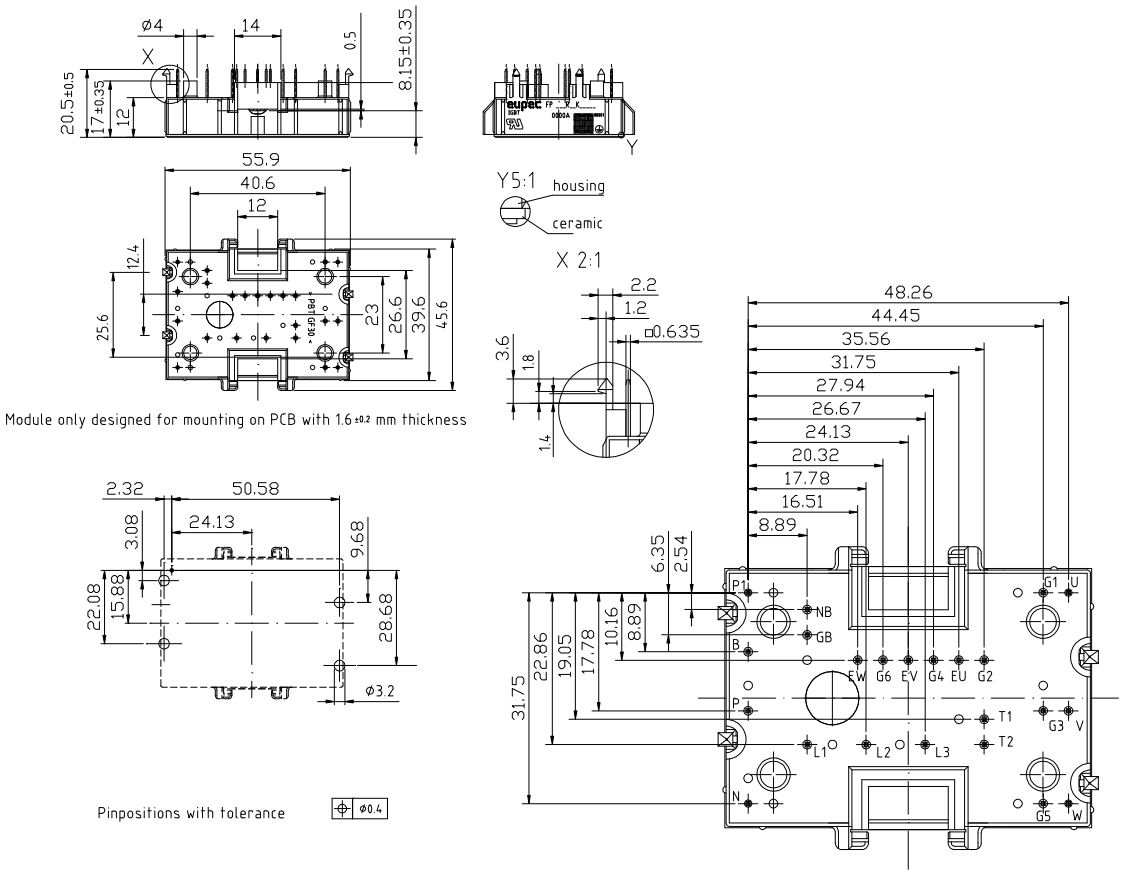
**Vorläufige Daten**
**preliminary data**

## Schaltplan / circuit diagram




## Gehäuseabmessungen / package outlines

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**Vorläufige Daten**
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